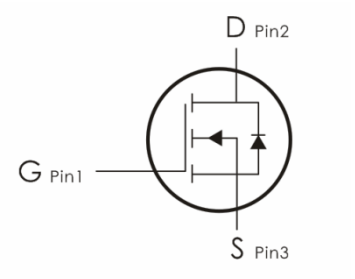
Description：

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.





Features：

1) V_{DS}=100V,I_D=50A,$R_{DS(ON)}$<22mΩ @V_{GS}=10V
2) Low gate charge.
3) Green device available.
4) Advanced high cell denity trench technology for ultra $R_{DS(ON)}$.
5) Excellent package for good heat dissipation.

Absolute Maximum Ratings： (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Continuous Drain Current- TC=25℃	50	A
	Continuous Drain Current-TC=100℃	30	
I_{DM}	Pulsed Drain Current	200	
I_{AR}	Avalanche Current	15	A
E_{AS}	Single Pulse Avalanche Energy	170	mJ
P_D	Power Dissipation	160	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	℃

Thermal Characteristics：

Symbol	Parameter	Max	Units
$R_{\theta JA}$	Junction to Ambient	40	℃/W

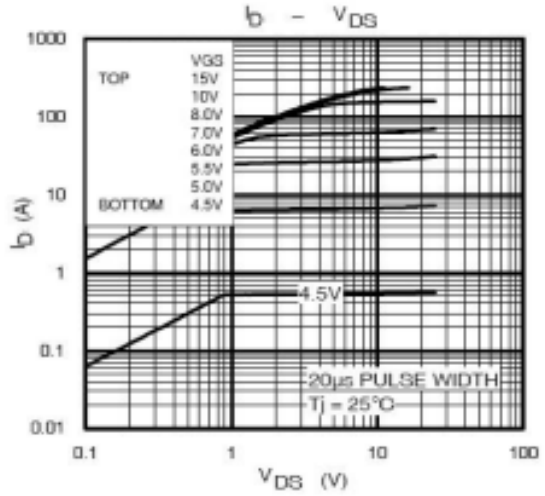
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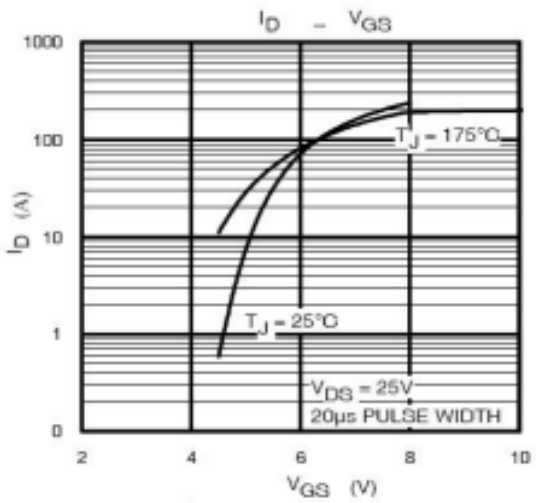
Electrical Characteristics: (T_C=25℃ unless otherwise noted)

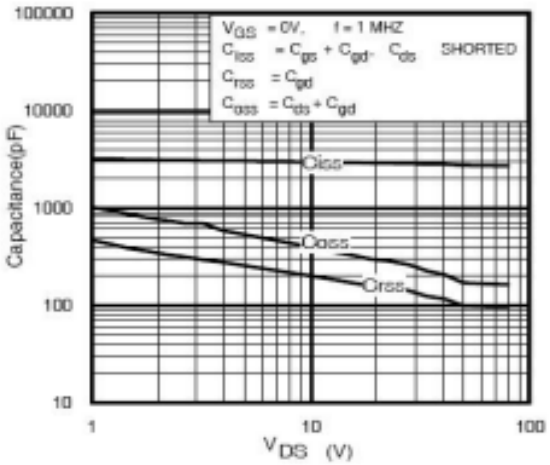
Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Sourtce Breakdown Voltage	V_{GS}=0V,I_D=250μA	100	---	---	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{GS}=0V, V_{DS}=100V	---	---	10	μA
		V_{GS}=0V, V_{DS}=100V,Tj=125℃	---	---	250	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V, V_{DS}=0A	---	---	±0.2	nA
On Characteristics						
$V_{GS(th)}$	GATE-Source Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	2	---	4	V
$R_{DS(ON)}$	Drain-Source On Resistance	V_{GS}=10V,I_D=1A	---	18	22	mΩ
G_{FS}	Forward Transconductance	V_{DS}=15V, I_D=10A, ΔI_D=1A	---	---	25	S
V_{SD}	Forward On Voltage	V_{GS}=0V I_S=35A T_J=25℃	---	---	1.3	V
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=25V, V_{GS}=0V, f=1MHz	---	2900	---	pF
C_{oss}	Output Capacitance		---	290	---	
C_{rss}	Reverse Transfer Capacitance		---	150	---	
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=50V, I_D=35A, R_{GEN}=6.8Ω .V_{GS}=10V	---	17	---	ns
t_r	Rise Time		---	77	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	41	---	ns
t_f	Fall Time		---	56	---	ns

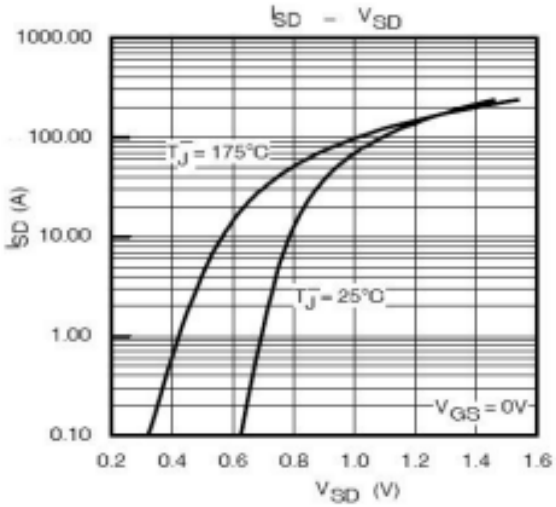
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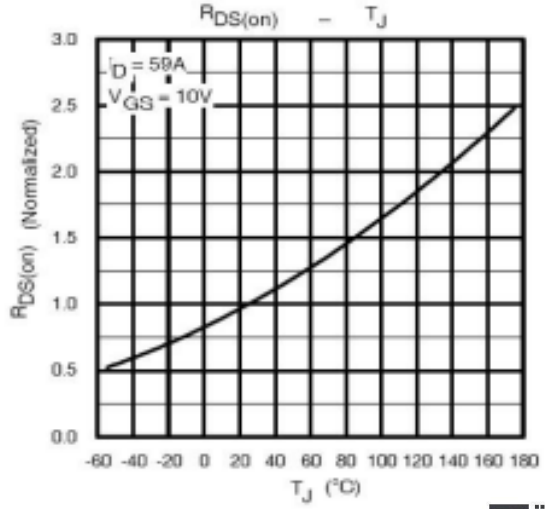
Typical Characteristics: (T_C=25℃ unless otherwise noted)

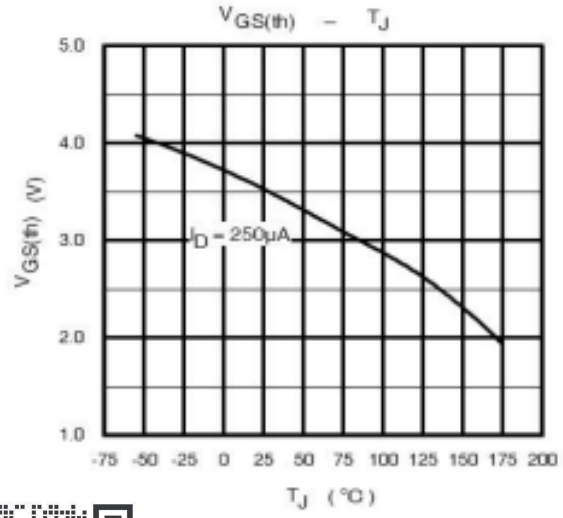












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